

10V Drive Nch MOSFET

RSJ400N06

● Structure

Silicon N-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) High current
- 3) High power Package

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	1000
RSJ400N06		○

● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	Continuous	I_D	± 40	A
	Pulsed	I_{DP} *1	± 80	A
Source current (Body Diode)	Continuous	I_S	40	A
	Pulsed	I_{SP} *1	80	A
Power dissipation		P_D *2	50	W
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Range of storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

*1 $P_w \leq 10\text{W}$, Duty cycle $\leq 1\%$

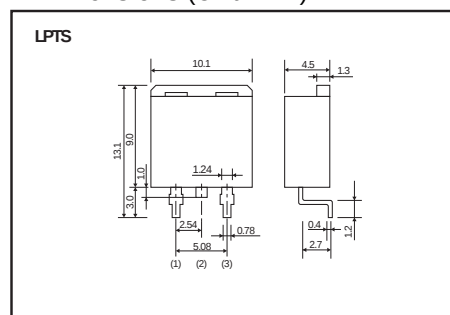
*2 $T_c = 25^\circ\text{C}$

● Thermal resistance

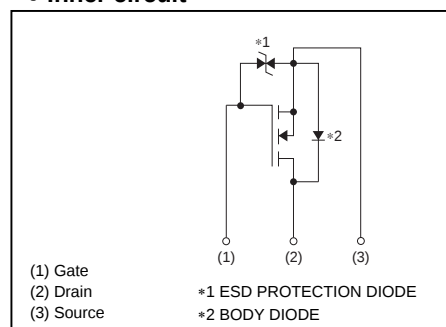
Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th(ch-c)}$ *	2.5	$^\circ\text{C} / \text{W}$

* $T_c = 25^\circ\text{C}$

● Dimensions (Unit : mm)



● Inner circuit



●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	60	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =60V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	R _{DS(on)} *	-	11	16	mΩ	I _D =40A, V _{GS} =10V
Forward transfer admittance	Y _{fs} *	14	-	-	S	I _D =20A, V _{DS} =10V
Input capacitance	C _{iss}	-	2400	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	490	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	250	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	20	-	ns	I _D =20A, V _{DD} ≒ 30V
Rise time	t _r *	-	60	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	-	90	-	ns	R _L =1.5Ω
Fall time	t _f *	-	140	-	ns	R _G =10Ω
Total gate charge	Q _g *	-	52	-	nC	V _{DD} ≒ 30V
Gate-source charge	Q _{gs} *	-	8	-	nC	I _D =40A,
Gate-drain charge	Q _{gd} *	-	15	-	nC	V _{GS} =10V

*Pulsed

●Body diode characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V _{SD} *	-	-	1.2	V	I _S =40A, V _{GS} =0V

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Static Drain-Source On-State Resistance vs. Drain Current

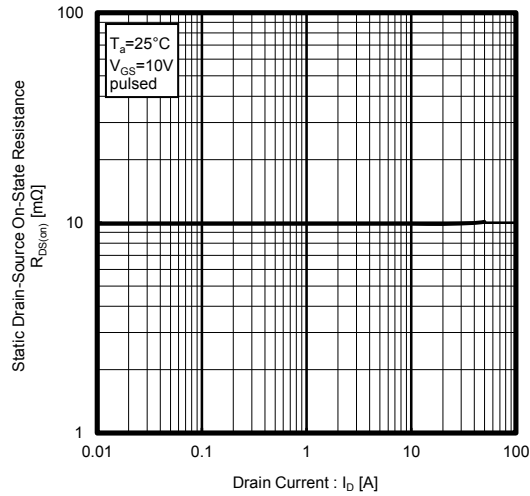


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

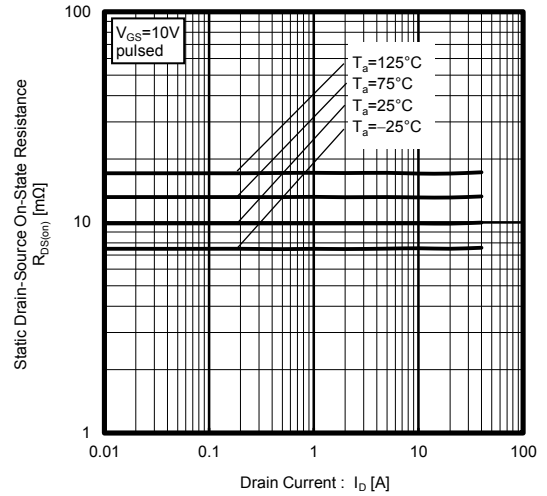


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

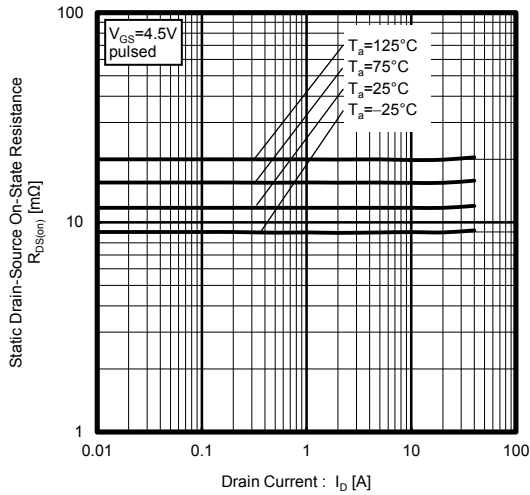


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

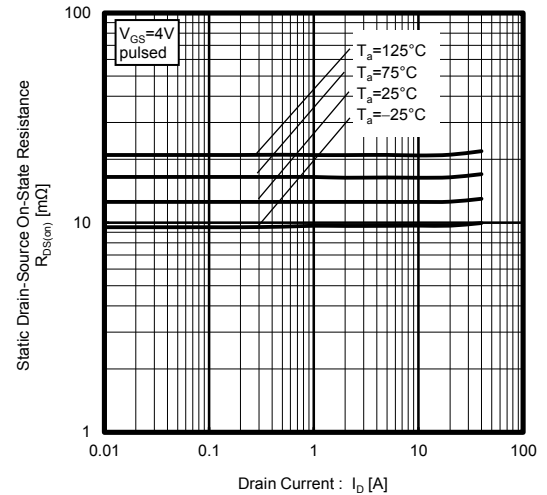


Fig.5 Forward Transfer Admittance vs. Drain Current

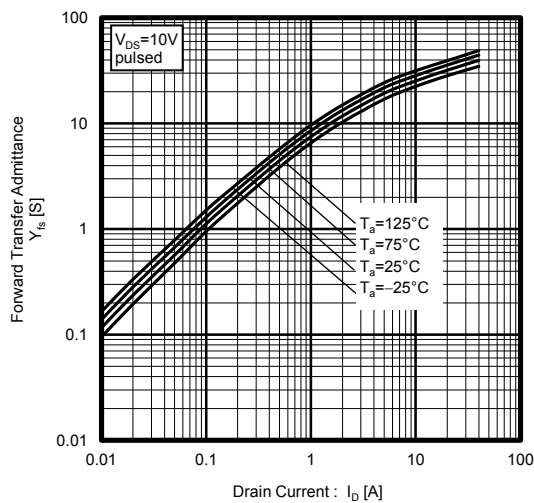


Fig.6 Typical Transfer Characteristics

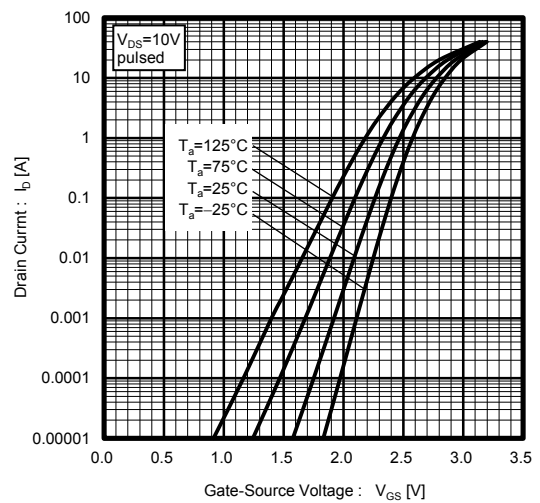


Fig.7 Source Current vs. Source-Drain Voltage

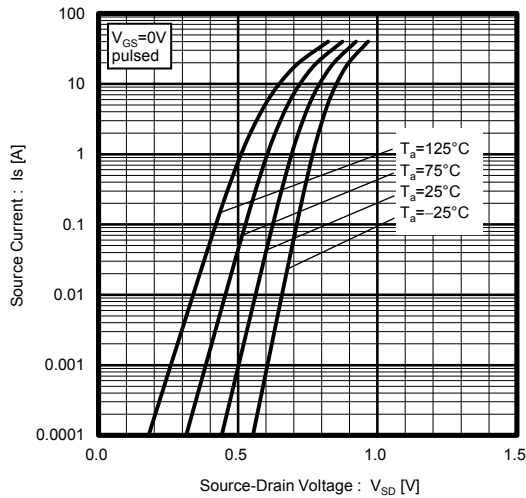


Fig.8 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

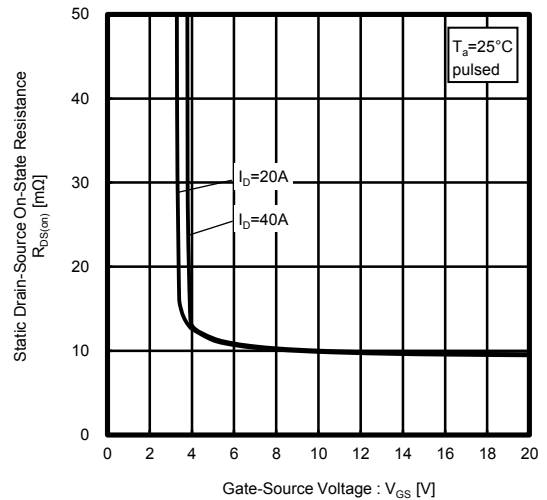


Fig.9 Switching Characteristics

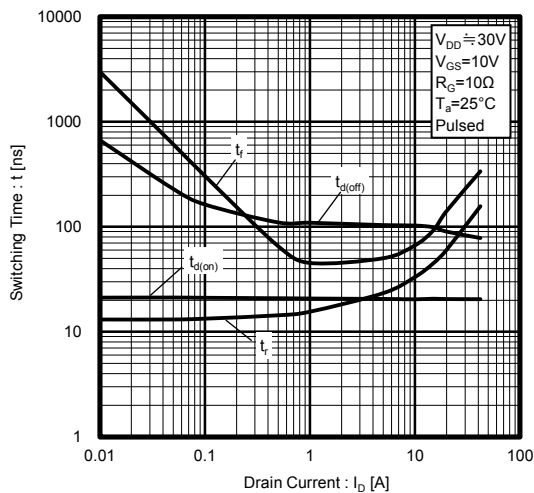


Fig.10 Dynamic Input Characteristics

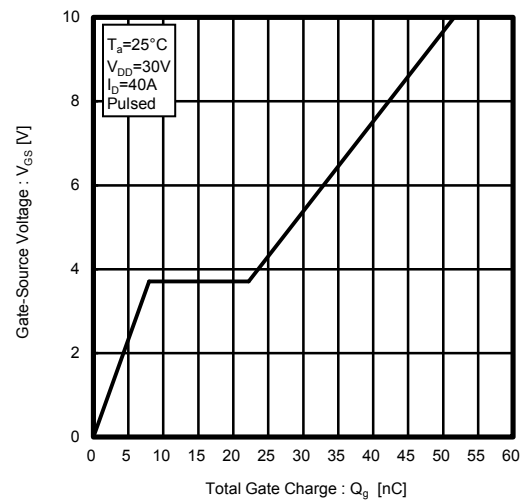


Fig.11 Typical Capacitance vs. Drain-Source Voltage

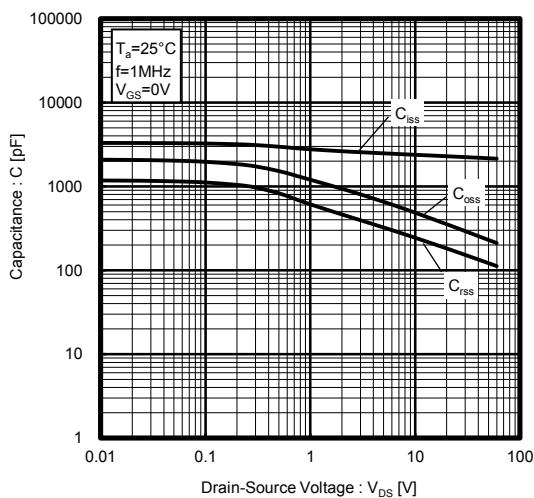
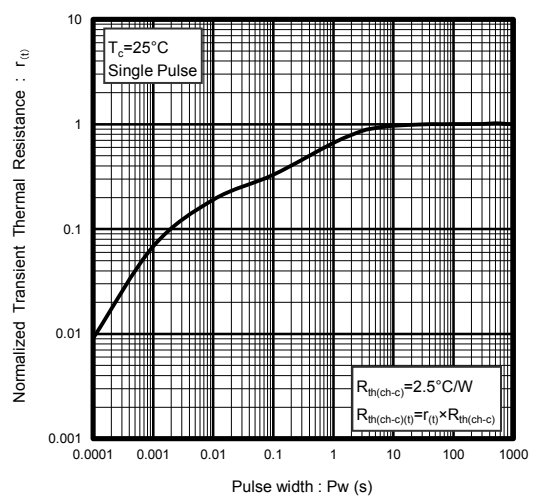


Fig.12 Normalized Transient Thermal Resistance v.s. Pulse Width



● Measurement circuits

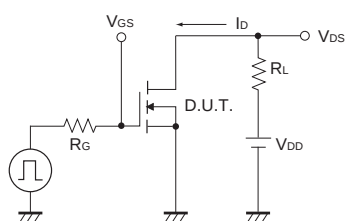


Fig.1-1 Switching Time Measurement Circuit

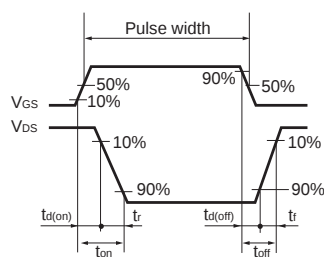


Fig.1-2 Switching Waveforms

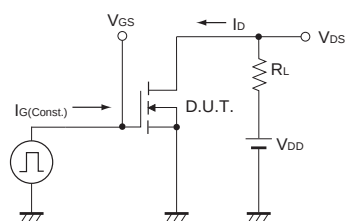


Fig.2-1 Gate Charge Measurement Circuit

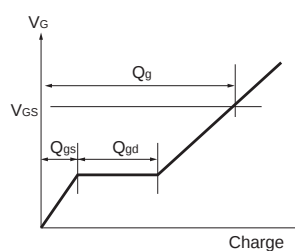


Fig.2-2 Gate Charge Waveform

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